

N-channel 25 V 2.4 mΩ logic level MOSFET in LFPAK using NextPower technology

Rev. 1 — 2 May 2011

**Product data sheet** 

### 1. Product profile

### 1.1 General description

Logic level enhancement mode N-channel MOSFET in LFPAK package. This product is designed and qualified for use in a wide range of industrial, communications and domestic equipment.

### 1.2 Features and benefits

- High reliability Power SO8 package, qualified to 175°C
- Low parasitic inductance and resistance

### **1.3 Applications**

- DC-to-DC converters
- Lithium-ion battery protection
- Load switching

### 1.4 Quick reference data

#### Table 1. Quick reference data

- Optimised for 4.5V Gate drive utilising NextPower Superjunction technology
- Ultra low QG, QGD and QOSS for high system efficiencies at low and high loads
- Power OR-ing
- Server power supplies
- Sync rectifier

Table 1.	QUICK reference (	lala				
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$V_{DS}$	drain-source voltage	25 °C ≤ T <sub>j</sub> ≤ 175 °C	-	-	25	V
I <sub>D</sub>	drain current	T <sub>mb</sub> = 25 °C; V <sub>GS</sub> = 10 V; see <u>Figure 1</u>	<u>[1]</u> _	-	100	А
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; see <u>Figure 2</u>	-	-	106	W
Tj	junction temperature		-55	-	175	°C
Static cha	aracteristics					
R <sub>DSon</sub>	drain-source on-state	V <sub>GS</sub> = 4.5 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 25 °C; see <u>Figure 12</u>	-	2.6	3.15	mΩ
	resistance	V <sub>GS</sub> = 10 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 25 °C; see <u>Figure 12</u>	-	2	2.4	mΩ



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Table 1.	Quick reference dat	acontinued				
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Dynamic	characteristics					
$Q_{GD}$	gate-drain charge	$\label{eq:VGS} \begin{array}{l} V_{GS} = 4.5 \; V; \; I_{D} = 25 \; A; \\ V_{DS} = 12 \; V; \; see \; \underline{Figure \; 14}; \\ see \; \underline{Figure \; 15} \end{array}$	-	5.2	-	nC
Q <sub>G(tot)</sub>	total gate charge	$V_{GS} = 4.5 \text{ V}; I_D = 25 \text{ A};$ $V_{DS} = 12 \text{ V}; \text{ see } \underline{\text{Figure } 15};$ $\text{see } \underline{\text{Figure } 14}$	-	18	-	nC

[1] Continuous current is limited by package

### 2. Pinning information

#### Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S	source		-
2	S	source	mb	
3	S	source		
4	G	gate	q;	
mb	D	mounting base; connected to drain	$ \begin{array}{cccccccccccccccccccccccccccccccccccc$	mbb076 S
			SOT669 (LFPAK;	

Power-SO8)

### 3. Ordering information

Table 3. O	Ordering information			
Type numbe	er	Package		
		Name	Description	Version
PSMN2R2-25	5YLC	LFPAK; Power-SO8	plastic single-ended surface-mounted package; 4 leads	SOT669

### 4. Marking

Table 4.   Marking codes	
Type number	Marking code <sup>[1]</sup>
PSMN2R2-25YLC	2C225L

[1] % = placeholder for manufacturing site code.

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### 5. Limiting values

#### Table 5. Limiting values

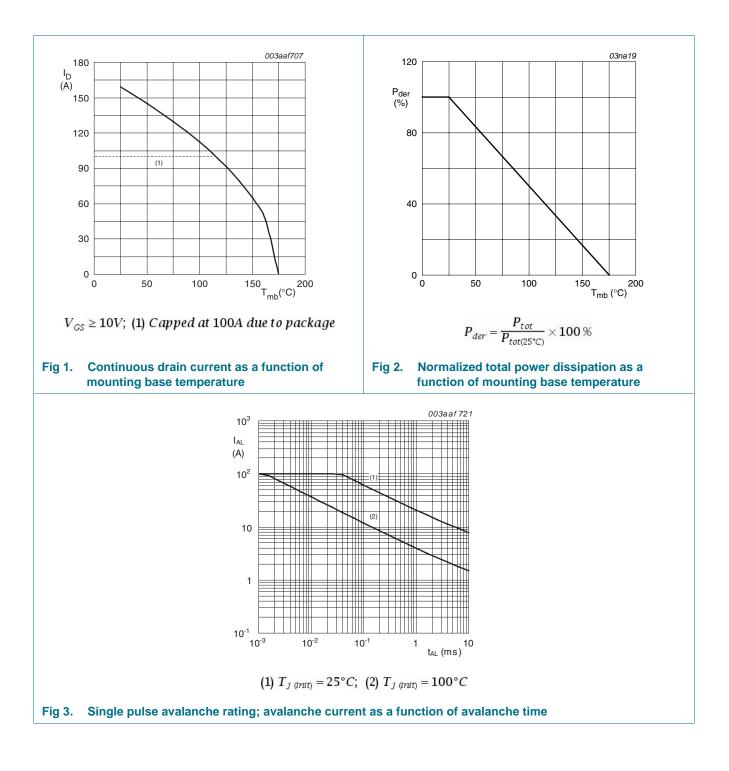
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Мах	Unit
V <sub>DS</sub>	drain-source voltage	25 °C ≤ T <sub>j</sub> ≤ 175 °C	-	25	V
V <sub>DGR</sub>	drain-gate voltage	25 °C $\leq$ T <sub>j</sub> $\leq$ 175 °C; R <sub>GS</sub> = 20 k $\Omega$	-	25	V
V <sub>GS</sub>	gate-source voltage		-20	20	V
I <sub>D</sub>	drain current	$V_{GS}$ = 10 V; $T_{mb}$ = 25 °C; see <u>Figure 1</u>	<u>[1]</u> _	100	А
		$V_{GS}$ = 10 V; $T_{mb}$ = 100 °C; see <u>Figure 1</u>	<u>[1]</u> _	100	А
I <sub>DM</sub>	peak drain current	pulsed; t <sub>p</sub> ≤ 10 µs; T <sub>mb</sub> = 25 °C; see <u>Figure 4</u>	-	636	А
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; see <u>Figure 2</u>	-	106	W
T <sub>stg</sub>	storage temperature		-55	175	°C
Tj	junction temperature		-55	175	°C
T <sub>sld(M)</sub>	peak soldering temperature		-	260	°C
V <sub>ESD</sub>	electrostatic discharge voltage	MM (JEDEC JESD22-A115)	430	-	V
Source-drain	diode				
I <sub>S</sub>	source current	T <sub>mb</sub> = 25 °C	-	96	А
I <sub>SM</sub>	peak source current	pulsed; $t_p \le 10 \ \mu s$ ; $T_{mb} = 25 \ ^{\circ}C$	-	636	А
Avalanche rug	gedness				
E <sub>DS(AL)S</sub>	non-repetitive drain-source avalanche energy	$V_{GS}$ = 10 V; $T_{j(init)}$ = 25 °C; $I_D$ = 100 A; $V_{sup}$ ≤ 25 V; unclamped; $R_{GS}$ = 50 Ω; see Figure 3	-	60	mJ

[1] Continuous current is limited by package.

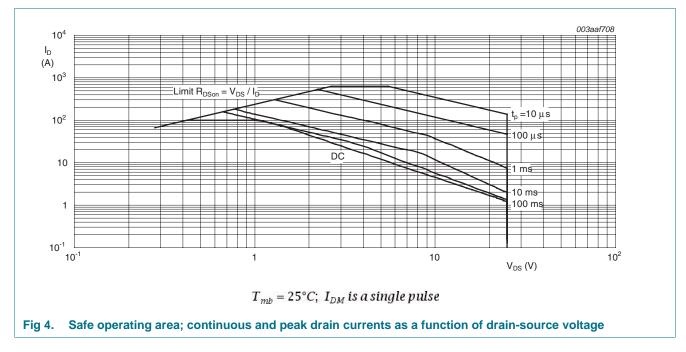
# PSMN2R2-25YLC

### N-channel 25 V 2.4 mΩ logic level MOSFET in LFPAK using NextPower



## PSMN2R2-25YLC

#### N-channel 25 V 2.4 mΩ logic level MOSFET in LFPAK using NextPower



### 6. Thermal characteristics

#### Table 6.Thermal characteristics

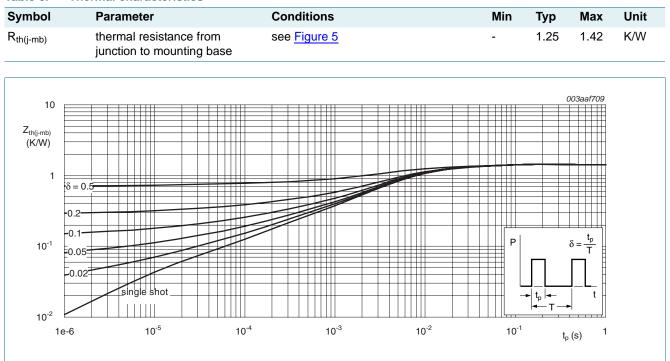


Fig 5. Transient thermal impedance from junction to mounting base as a function of pulse duration

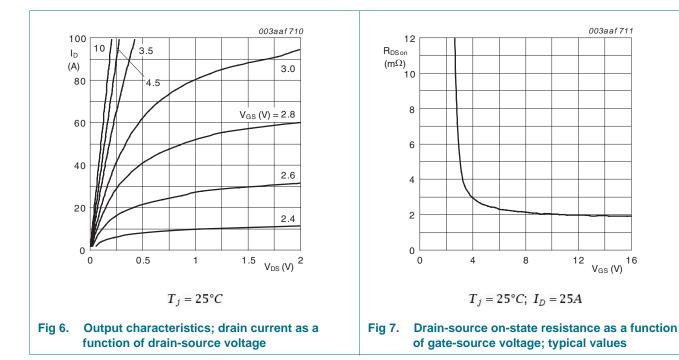
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### 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	cteristics					
V <sub>(BR)DSS</sub>	drain-source	I <sub>D</sub> = 250 μA; V <sub>GS</sub> = 0 V; T <sub>i</sub> = 25 °C	25	-	-	V
<b>、</b> ,	breakdown voltage	I <sub>D</sub> = 250 μA; V <sub>GS</sub> = 0 V; T <sub>i</sub> = -55 °C	22.5	-	-	V
V <sub>GS(th)</sub>	gate-source threshold voltage	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ °C};$ see Figure 10; see Figure 11	1.05	1.54	1.95	V
		I <sub>D</sub> = 10 mA; V <sub>DS</sub> = V <sub>GS</sub> ; T <sub>j</sub> = 150 °C	0.5	-	-	V
		I <sub>D</sub> = 1 mA; V <sub>DS</sub> = V <sub>GS</sub> ; T <sub>j</sub> = -55 °C	-	-	2.25	V
I <sub>DSS</sub>	drain leakage current	V <sub>DS</sub> = 25 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	1	μA
		$V_{DS} = 25 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 150 \text{ °C}$	-	-	100	μA
I <sub>GSS</sub> gate	gate leakage current	V <sub>GS</sub> = 16 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	100	nA
		$V_{GS}$ = -16 V; $V_{DS}$ = 0 V; $T_j$ = 25 °C	-	-	100	nA
Doon	drain-source on-state resistance	V <sub>GS</sub> = 4.5 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 25 °C; see <u>Figure 12</u>	-	2.6	3.15	mΩ
		V <sub>GS</sub> = 4.5 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 150 °C; see <u>Figure 13</u> ; see <u>Figure 12</u>	-	-	5.05	mΩ
		V <sub>GS</sub> = 10 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 25 °C; see <u>Figure 12</u>	-	2	2.4	mΩ
		V <sub>GS</sub> = 10 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 150 °C; see <u>Figure 13</u> ; see <u>Figure 12</u>	-	-	3.85	mΩ
R <sub>G</sub>	gate resistance	f = 1 MHz	-	0.9	1.8	Ω
Dynamic ch	aracteristics					
Q <sub>G(tot)</sub> total gate charge	total gate charge	$I_D$ = 25 A; $V_{DS}$ = 12 V; $V_{GS}$ = 10 V; see <u>Figure 14</u> ; see <u>Figure 15</u>	-	39	-	nC
		$I_D$ = 25 A; $V_{DS}$ = 12 V; $V_{GS}$ = 4.5 V; see <u>Figure 15</u> ; see <u>Figure 14</u>	-	18	-	nC
		$I_D = 0 \text{ A}; \text{ V}_{DS} = 0 \text{ V}; \text{ V}_{GS} = 10 \text{ V}$	-	38	-	nC
Q <sub>GS</sub>	gate-source charge	$I_D = 25 \text{ A}; V_{DS} = 12 \text{ V}; V_{GS} = 4.5 \text{ V};$	-	6.3	-	nC
Q <sub>GS(th)</sub>	pre-threshold gate-source charge	see <u>Figure 14</u> ; see <u>Figure 15</u>	-	4.1	-	nC
Q <sub>GS(th-pl)</sub>	post-threshold gate-source charge		-	2.2	-	nC
Q <sub>GD</sub>	gate-drain charge		-	5.2	-	nC
V <sub>GS(pl)</sub>	gate-source plateau voltage	$I_D = 25 \text{ A}; V_{DS} = 12 \text{ V}; \text{ see } \frac{\text{Figure } 14}{\text{Figure } 15}$	-	2.7	-	V
C <sub>iss</sub>	input capacitance	$V_{DS} = 12 \text{ V}; V_{GS} = 0 \text{ V}; f = 1 \text{ MHz};$	-	2542	-	pF
C <sub>oss</sub>	output capacitance	$T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure } 16}{16}$	-	617	-	pF
C <sub>rss</sub>	reverse transfer capacitance		-	216	-	pF
t <sub>d(on)</sub>	turn-on delay time	$V_{DS}$ = 12 V; $R_L$ = 0.5 Ω; $V_{GS}$ = 4.5 V;	-	24	-	ns
t <sub>r</sub>	rise time	$R_{G(ext)} = 4.7 \Omega$	-	34	-	ns
t <sub>d(off)</sub>	turn-off delay time		-	36	-	ns
t <sub>f</sub>	fall time		-	16	-	ns
SMN2R2-25YLC		All information provided in this document is subject to legal disclaimers.		@ N	eria B.V. 2017.	

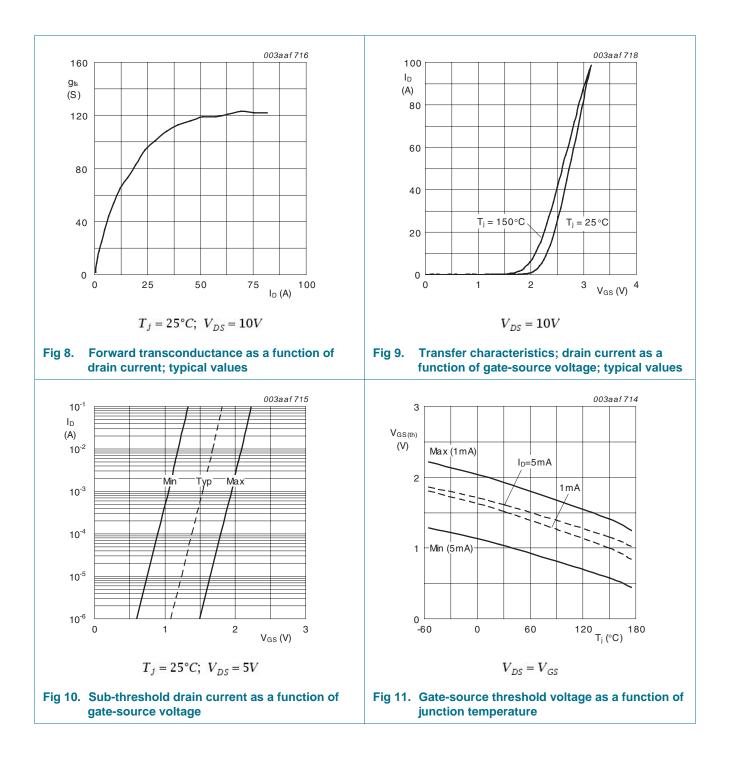
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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Q <sub>oss</sub>	output charge	$V_{GS} = 0 \text{ V}; V_{DS} = 12 \text{ V}; \text{ f} = 1 \text{ MHz};$ $T_j = 25 ^{\circ}\text{C}$	-	16.7	-	nC
Source-dra	iin diode					
V <sub>SD</sub>	source-drain voltage	I <sub>S</sub> = 25 A; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C; see <u>Figure 17</u>	-	0.8	1.1	V
t <sub>rr</sub>	reverse recovery time	$I_{S} = 25 \text{ A}; \text{ dI}_{S}/\text{dt} = -100 \text{ A}/\mu\text{s}; \text{ V}_{GS} = 0 \text{ V};$	-	35	-	ns
Q <sub>r</sub>	recovered charge	$V_{DS} = 12 V$	-	31	-	nC
t <sub>a</sub>	reverse recovery rise time	$V_{GS} = 0 \text{ V}; \text{ I}_S = 25 \text{ A}; \text{ dI}_S/\text{dt} = -100 \text{ A}/\mu\text{s};$ $V_{DS} = 12 \text{ V}; \text{ see } \frac{\text{Figure } 18}{100000000000000000000000000000000000$	-	21	-	ns
t <sub>b</sub>	reverse recovery fall time		-	14	-	ns



# PSMN2R2-25YLC

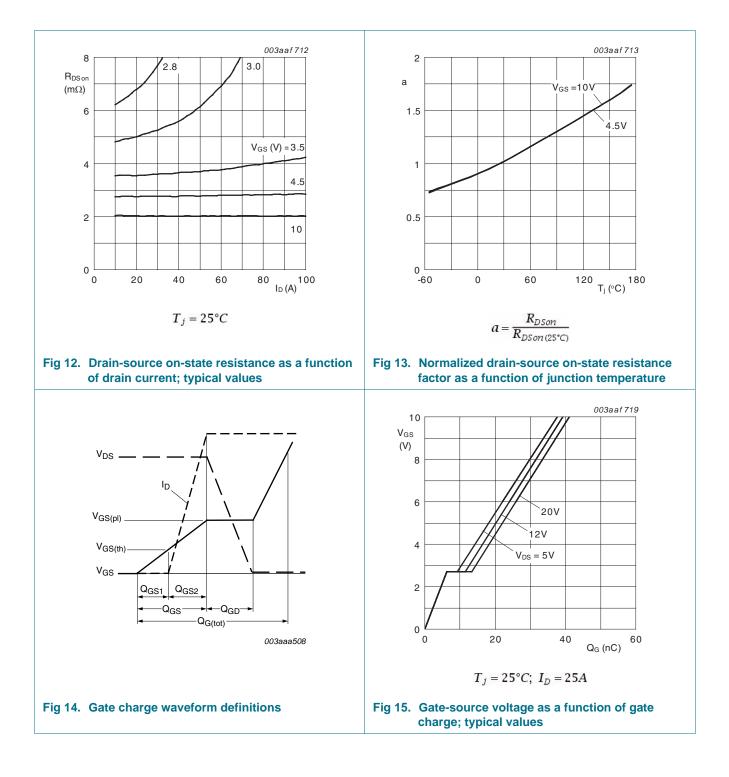
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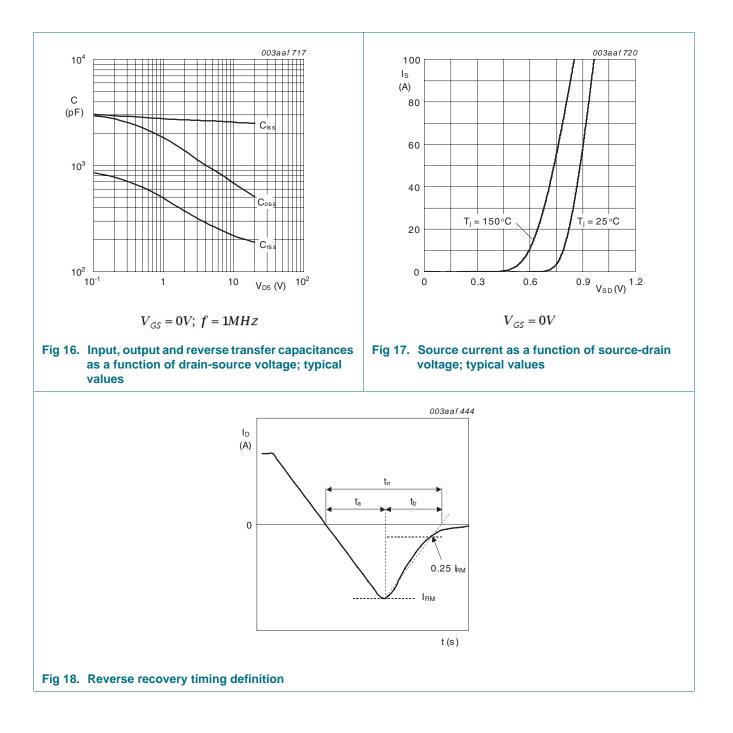
# PSMN2R2-25YLC

### N-channel 25 V 2.4 mΩ logic level MOSFET in LFPAK using NextPower



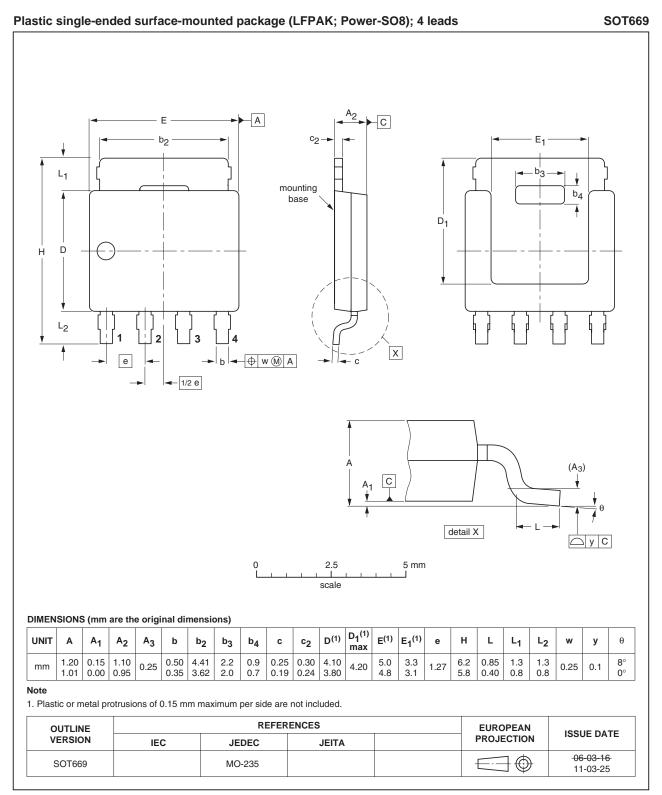
## PSMN2R2-25YLC

### N-channel 25 V 2.4 mΩ logic level MOSFET in LFPAK using NextPower



#### N-channel 25 V 2.4 mΩ logic level MOSFET in LFPAK using NextPower

### 8. Package outline



#### Fig 19. Package outline SOT669 (LFPAK; Power-SO8)

PSMN2R2-25YLC Product data sheet

### N-channel 25 V 2.4 mΩ logic level MOSFET in LFPAK using NextPower

## 9. Revision history

Table 8. Revision h	Cable 8.         Revision history				
Document ID	Release date	Data sheet status	Change notice	Supersedes	
PSMN2R2-25YLC v.1	20110502	Product data sheet	-	-	

### **10. Legal information**

### **10.1 Data sheet status**

Document status [1] [2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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